

INFRARED DIODE LASER AT 860nm

RN-III-860/1~1000mW

产品描述

It features ultra compact design, long lifetime, cost-effectiveness and easy operation. They are used in measurement, communication, spectrum analysis, etc.

产品参数

RN-III-860/1~1000mW		
Central wavelength (nm)	785±10	
Operating mode	CW	
Output power (mW)	>1, 50, 100, ... , 2500	
Power stability (rms, over 4 hours)	<1%, <2%, <3% (<0.5%, optional)	
Transverse mode	Multimode	
Dimensions of beam at the aperture (mm)	~5×8	
Beam divergence, full angle (mrad)	<3.0	
Warm-up time (minutes)	<5	
Beam height from base plate (mm)	24.8	
Operating temperature (°C)	10~35	
Power supply	85-264VAC	PSU-III-LED/ PSU-III-FDA (Frequency for 1Hz-30kHz)
	100-240VAC	PSU-A-D (Frequency for 30kHz -100kHz)
TTL / Analog modulation	TTL or Analog with 1Hz-1kHz 1kHz-10kHz, 10kHz-30kHz, 30kHz-100kHz optional	
Expected lifetime (hours)	1 year	
Warranty period	1 year	